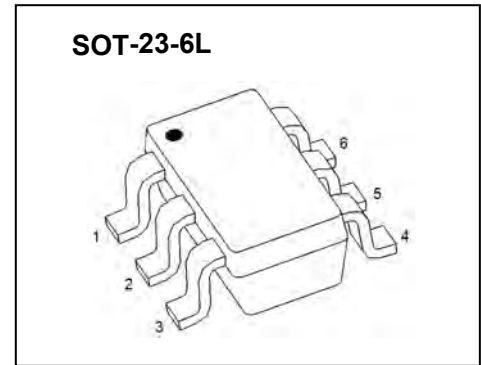


Plastic-Encapsulate MOSFETS

Dual N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
19V	25mΩ@4.5V	6A
	32mΩ@2.5V	



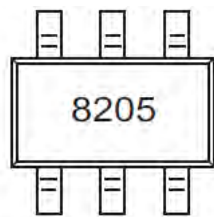
FEATURE

- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$
- Low Gate Charge
- High Power and Current Handling Capability
- Surface Mount Package

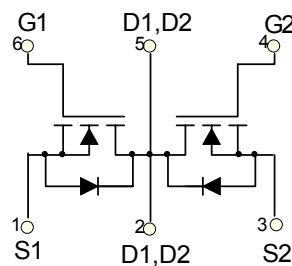
APPLICATION

- Battery Protection
- Load Switch
- Power Management

MARKING



Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	19	V
Gate-Source Voltage	V_{GS}	±10	V
Continuous Drain Current	I_D	6	A
Pulsed Drain Current (note 1)	I_{DM}	25	A
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	19			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 18V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage (note 3)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5		0.9	V
Drain-source on-resistance (note 3)	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 6A$			25	m Ω
		$V_{GS} = 2.5V, I_D = 5A$			32	m Ω
Forward transconductance (note 3)	g_{FS}	$V_{DS} = 5V, I_D = 4.5A$		10		S
Diode forward voltage (note 3)	V_{SD}	$I_S = 1.25A, V_{GS} = 0V$			1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input Capacitance	C_{iss}	$V_{DS} = 8V, V_{GS} = 0V, f = 1MHz$		800		pF
Output Capacitance	C_{oss}			155		pF
Reverse Transfer Capacitance	C_{rss}			125		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10V, V_{GS} = 4V,$ $I_D = 1A, R_{GEN} = 10\Omega$		18		ns
Turn-on rise time	t_r			5		ns
Turn-off delay time	$t_{d(off)}$			43		ns
Turn-off fall time	t_f			20		ns
Total Gate Charge	Q_g	$V_{DS} = 10V, V_{GS} = 4.5V, I_D = 4A$		11		nC
Gate-Source Charge	Q_{gs}			2.3		nC
Gate-Drain Charge	Q_{gd}			2.5		nC

Notes :

- 1.Repetitive rating: Pulse width limited by maximum junction temperature
- 2.Surface Mounted on FR4 board, $t \leq 10$ sec.
3. Pulse test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production.



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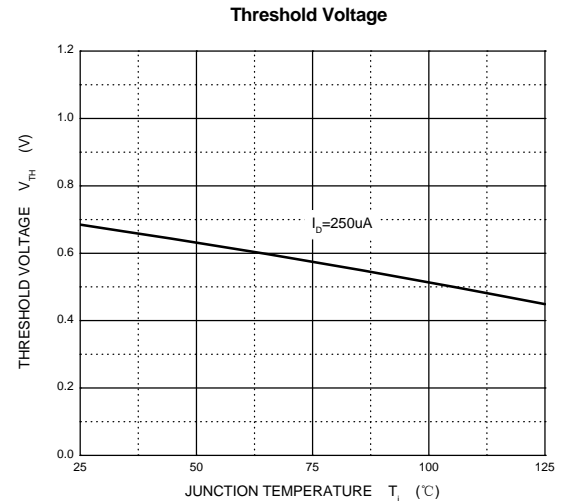
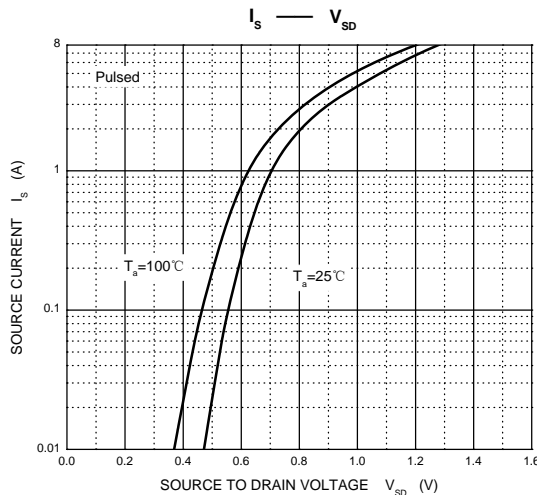
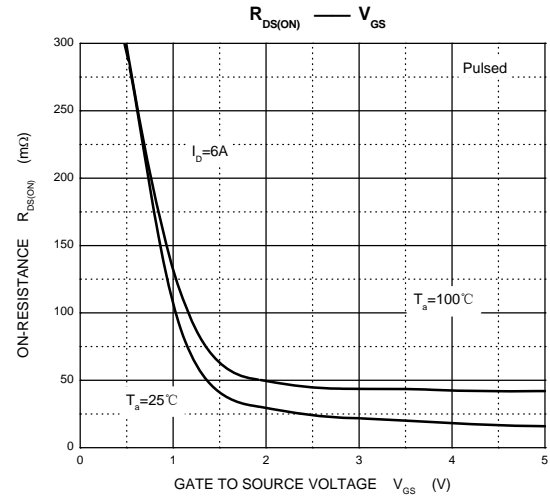
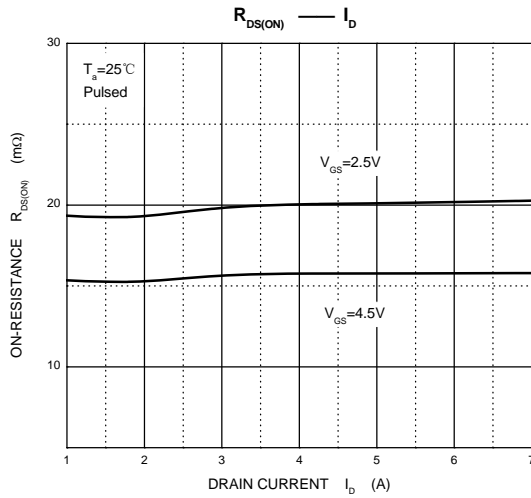
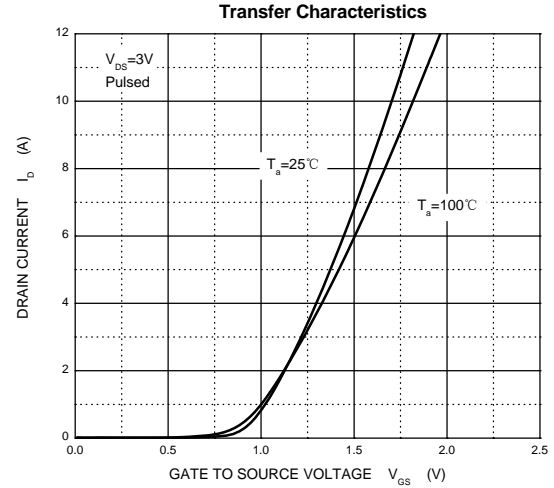
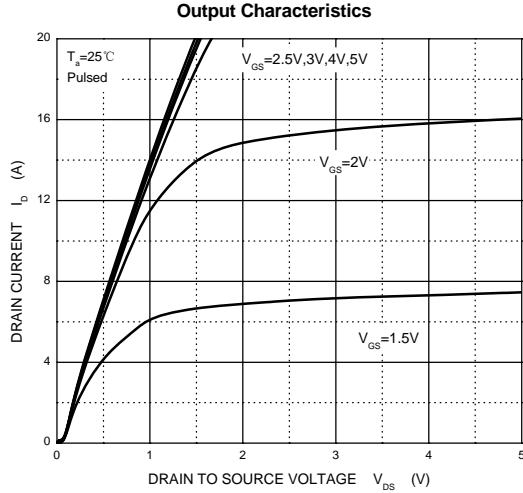
SOT-23-6L

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Typical Characteristics





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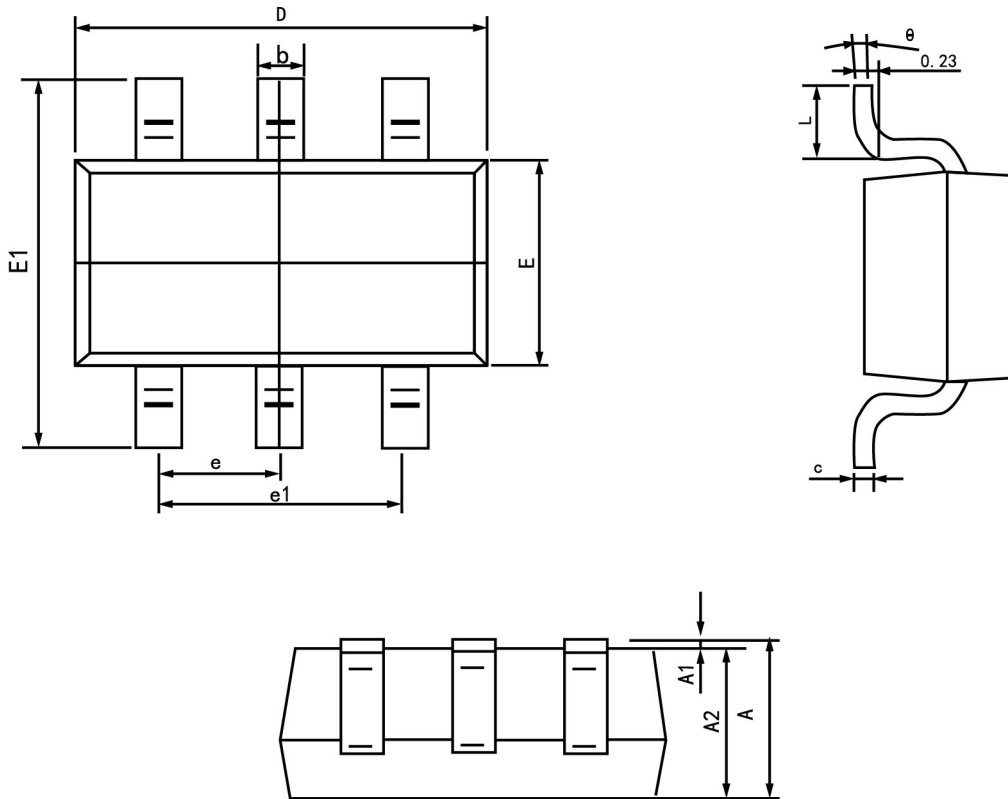
SOT-23-6L

BC8205



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SOT-23-6L Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.820	3.020
E	1.500	1.700
E1	2.650	2.950
e	0.950 (Basic)	
e1	1.8	2.000
L	0.300	0.600
θ	0°	8°